

Low-Voltage Single SPDT MICRO FOOT® Analog Switch

DESCRIPTION

The DG3000 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 24 ns, t_{OFF} : 9 ns), low on-resistance ($r_{DS(on)}$: 1.4 Ω) and small physical size (MICRO FOOT, 6-bump), the DG3000 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG3000 is built on Vishay Siliconix's low voltage J12 process. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG3000.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switching products manufactured with tin/silver/copper (Sn/Ag/Cu) device terminations, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- MICRO FOOT® Chip Scale Package (1.07 x 1.57 mm)
- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - $r_{DS(on)}$: 1.4 Ω
- Fast Switching - t_{ON} : 24 ns, t_{OFF} : 9 ns
- Low Power Consumption
- TTL/CMOS Compatible



RoHS*
COMPLIANT

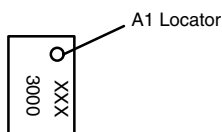
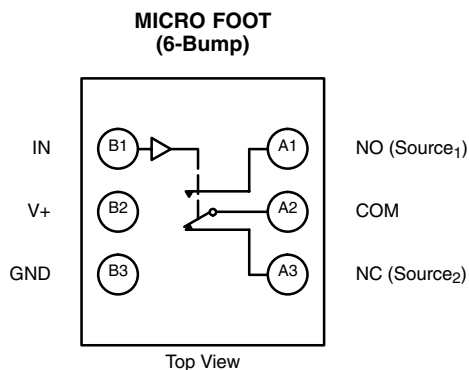
BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- PCM Cards
- PDA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: 3000
xxx = Date/Lot Traceability Code

TRUTH TABLE

Logic	NC	NO
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION

Temp Range	Package	Part Number
- 40 to 85 °C	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm Pitch 165 μ m nom. bump height (Eutectic, SnPb)	DG3000DB-T1
	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm pitch, 238 μ m nom. bump height (Lead (Pb)-free, Sn/Ag/Cu)	DG3000DB-T1-E1

* Pb containing terminations are not RoHS compliant, exemptions may apply.

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Limit	Unit
Referenced V_+ to GND	- 0.3 to + 6 V	V
IN, COM, NC, NO ^a	- 0.3 V to ($V_+ + 0.3$ V)	
Continuous Current (Any Terminal)	± 50	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)	± 200	
Storage Temperature (D Suffix)	- 65 to 150	$^\circ\text{C}$
Package Reflow Conditions^b		
VPR (Eutectic)	215	$^\circ\text{C}$
IR/Convection (Eutectic)	220	
IR/Convection (Lead (Pb)-free)	250	
Power Dissipation (Packages) ^c	6-Bump, 3 x 2 MICRO FOOT ^d	mW

Notes:

a. Signals on NC, NO, or COM or IN exceeding V_+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. Refer to IPC/JEDEC (J-STD-020A). No hand/manual solder rework recommended.

c. All bumps soldered to PC Board.

d. Derate 3.1 mW/ $^\circ\text{C}$ above 70°C .**SPECIFICATIONS ($V_+ = 2.0$ V)**

Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 2.0 V, ± 10 %, VIN = 0.4 or 1.6 V ^e	Temp ^a	Limits - 40 to 85 °C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 1.8 V, V _{COM} = 1.0 V, I _{NO} , I _{NC} = 10 mA	Room Full ^d		17	20 22.5	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 1.8 V, V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		14		
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 2.2 V V _{NO} , V _{NC} = 0.5 V/1.5 V, V _{COM} = 1.5 V/0.5 V	Room Full ^d	- 700 - 11		700 11	pA nA
	I _{COM(off)}		Room Full ^d	- 700 - 11		700 11	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V/1.5 V	Room Full ^d	- 700 - 11		700 11	pA nA
Digital Control							
Input High Voltage	V _{INH}		Full	1.6			V
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance ^d	C _{in}		Full		5		pF
Input Current ^d	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 300 Ω, C _L = 35 pF Figures 1 and 2	Room Full ^d		61	76 79	ns
Turn-Off Time	t _{OFF}		Room Full ^d		17	33 36	
Break-Before-Make Time	t _d		Room	1	45		
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω, Figure 3	Room		2		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		- 61		dB
Crosstalk ^d	X _{TALK}		Room		- 67		
NO, NC Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		31		pF
Channel-On Capacitance ^d	C _{ON}		Room		98		
Power Supply							
Power Supply Range	V+	V _{IN} = 0 or V+		1.8		2.2	V
Power Supply Current ^d	I+				0.1	1.0	μA
Power Consumption	P _C					2.2	μW



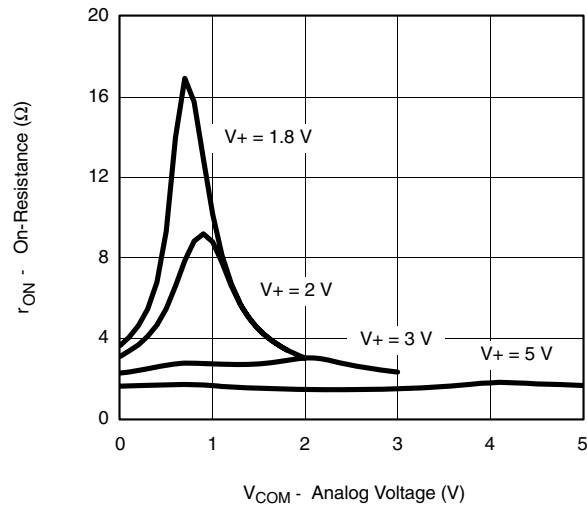
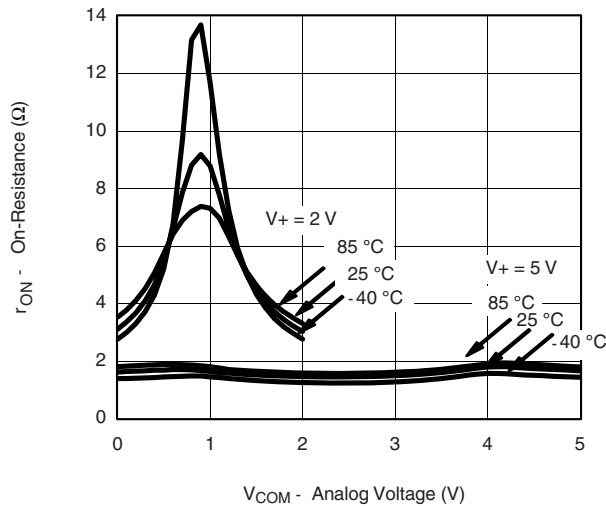
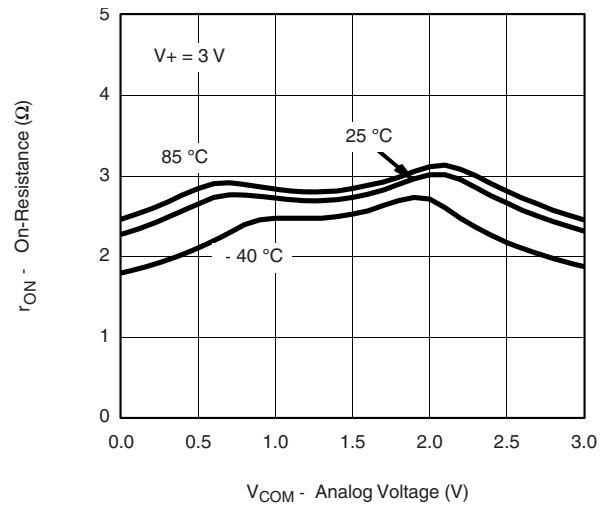
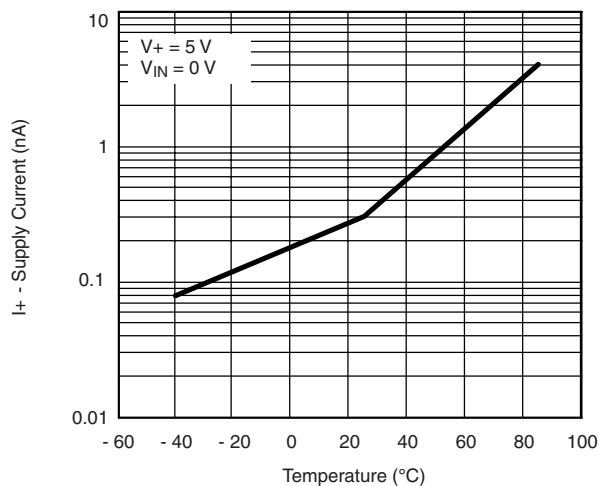
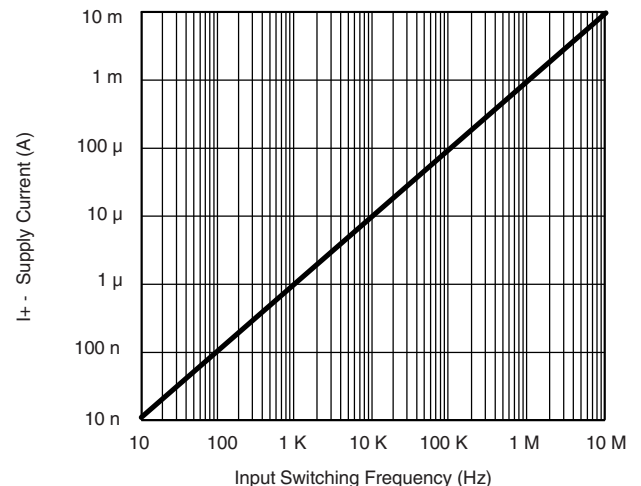
SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10 %, V _{IN} = 0.4 or 2.0 V ^e	Temp ^a	Limits - 40 to 85 °C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	V
On-Resistance ^d	r _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room Full		3.3 3.4	4.1 4.2	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 2.7 V, V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		1.3		
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V V _{NO} , V _{NC} = 1 V/3 V, V _{COM} = 3 V/1 V	Room Full	- 800 - 13		800 13	pA nA
	I _{COM(off)}		Room Full	- 800 - 13		800 13	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	- 800 - 13		800 13	pA nA
Digital Control							
Input High Voltage	V _{INH}		Full	2			V
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance ^d	C _{in}		Full		5		pF
Input Current ^d	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V _{NO} or V _{NC} = 2.0 V, R _L = 300 Ω, C _L = 35 pF Figures 1 and 2	Room Full		34	49 52	ns
Turn-Off Time ^d	t _{OFF}		Room Full		12	30 33	
Break-Before-Make Time ^d	t _d		Room	1	23		
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω, Figure 3	Room		4		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		- 61		dB
Crosstalk ^d	X _{TALK}		Room		- 67		
NO, NC Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		31		pF
Channel-On Capacitance ^d	C _{ON}		Room		47		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current ^d	I+	V _{IN} = 0 or V+			0.1	1.0	μA
Power Consumption	P _C						3.3

SPECIFICATIONS (V+ = 5.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5 V, ± 10 %, VIN = 0.8 or 2.4 V ^e	Temp ^a	Limits - 40 to 85 °C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	VNO, VNC VCOM		Full	0		V+	V
On- Resistance	rON	V+ = 4.5 V, VCOM = 3 V, INO, INC = 10 mA	Room Full		1.4 1.6	2.3 2.8	Ω
rON Flatness ^d	rON Flatness	V+ = 4.5 V, VCOM = 0 to V+, INO, INC = 10 mA	Room		0.5		
Switch Off Leakage Current	INO(off) INC(off)	V+ = 5.5 V VNO, VNC = 1 V/4.5 V, VCOM = 4.5 V/1 V	Room Full	- 1.2 - 21		1.2 21	nA
	ICOM(off)		Room Full	- 1.2 - 21		1.2 21	
Channel-On Leakage Current	ICOM(on)	V+ = 5.5 V, V+ = 5.5 V VNO, VNC = VCOM = 1 V/4.5 V	Room Full	- 1.2 - 21		1.2 21	
Digital Control							
Input High Voltage	VINH		Full	2.4			V
Input Low Voltage	VINL		Full			0.8	
Input Capacitance	Cin		Full		5		pF
Input Current	IINL or IINH	VIN = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	tON	VNO or VNC = 3 V, RL = 300 Ω, CL = 35 pF Figures 1 and 2	Room Full		24	36 39	ns
Turn-Off Time ^d	tOFF		Room Full		9	22 25	
Break-Before-Make Time ^d	td		Room	1	15		
Charge Injection ^d	QINJ	CL = 1 nF, VGEN = 0 V, RGEN = 0 Ω, Figure 3	Room		38		pC
Off-Isolation ^d	OIRR	RL = 50 Ω, CL = 5 pF, f = 1 MHz	Room		- 61		dB
Crosstalk ^d	XTALK		Room		- 67		
Source-Off Capacitance ^d	CNO(off) CNC(off)	VIN = 0 or V+, f = 1 MHz	Room		30		pF
Channel-On Capacitance ^d	CON		Room		96		
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	I+	VIN = 0 or V+			0.1	1.0	μA
Power Consumption	PC						5.5

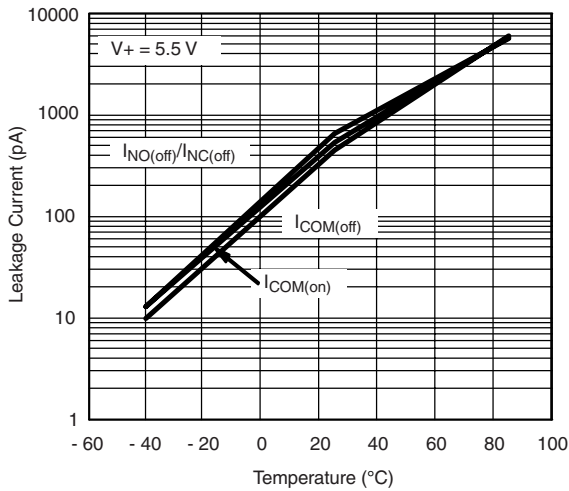
Notes:

- Room = 25 °C, Full = as determined by the operating suffix.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Typical values are for design aid only, not guaranteed nor subject to production testing.
- Guarantee by design, nor subjected to production test.
- V_{IN} = input voltage to perform proper function.
- Guaranteed by 5 V leakage testing, not production tested.

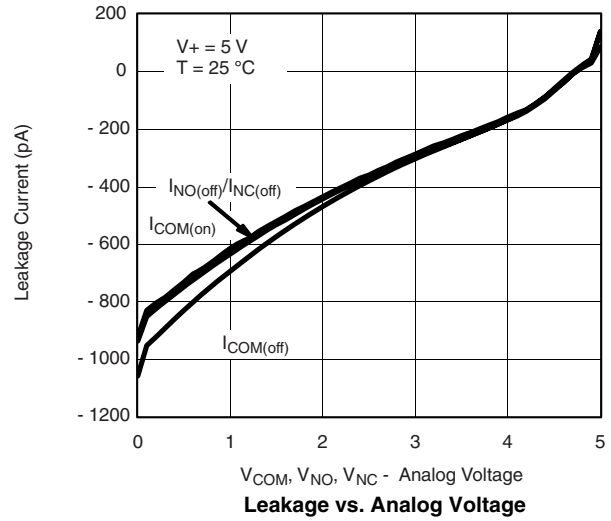
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 r_{ON} vs. V_{COM} and Supply Voltage

 r_{ON} vs. Analog Voltage and Temperature

 r_{ON} vs. Analog Voltage and Temperature

Supply Current vs. Temperature

Supply Current vs. Input Switching Frequency

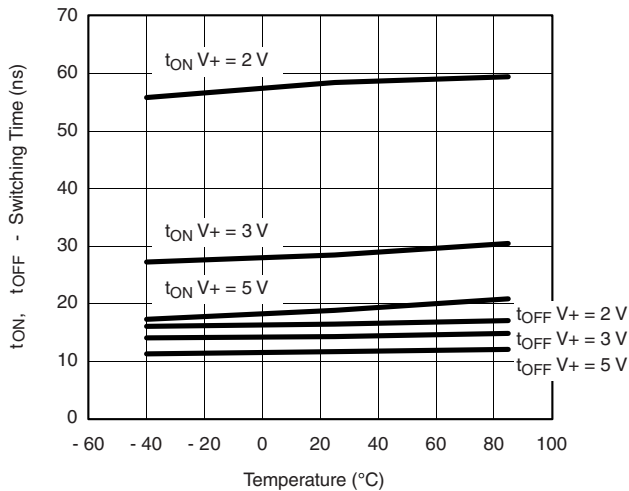
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



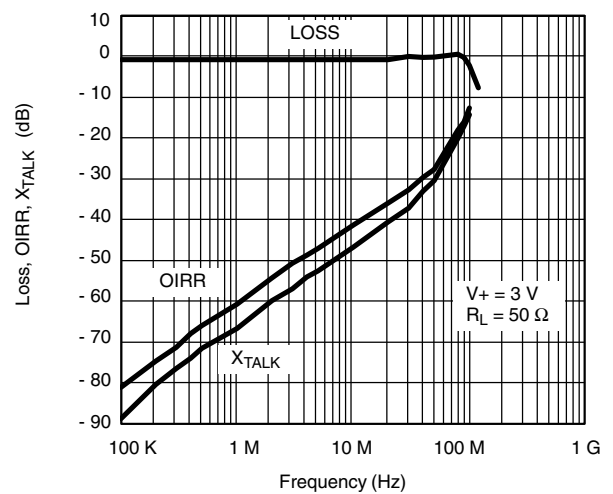
Leakage Current vs. Temperature



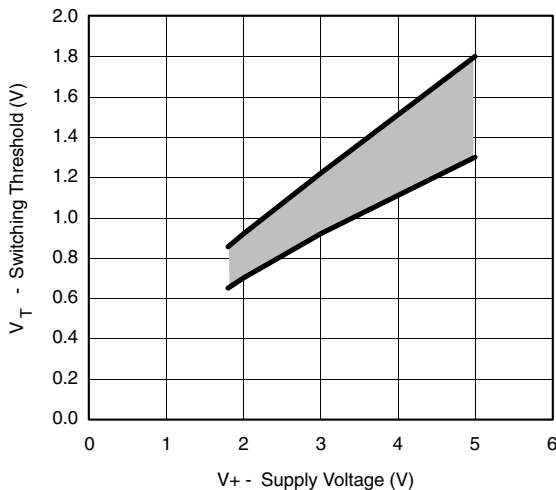
Leakage vs. Analog Voltage



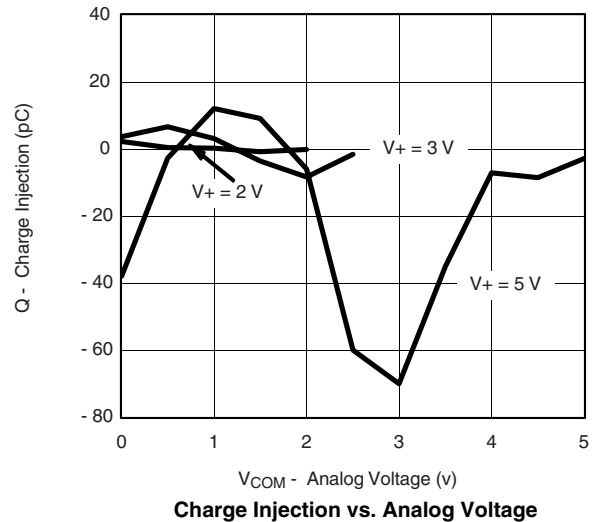
Switching Time vs. Temperature and Supply Voltage



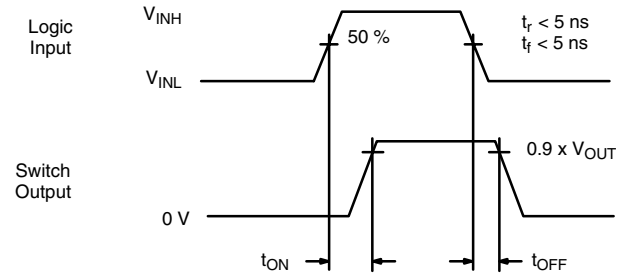
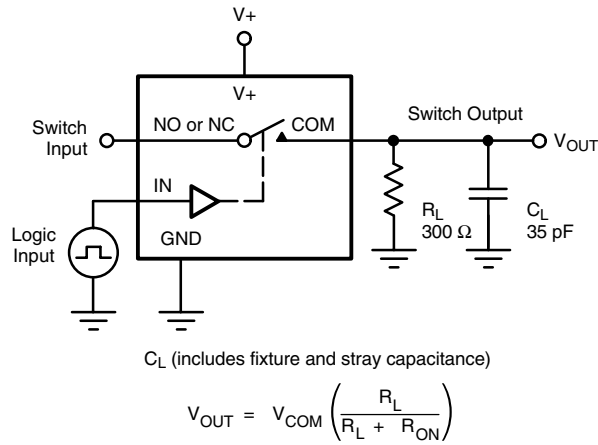
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



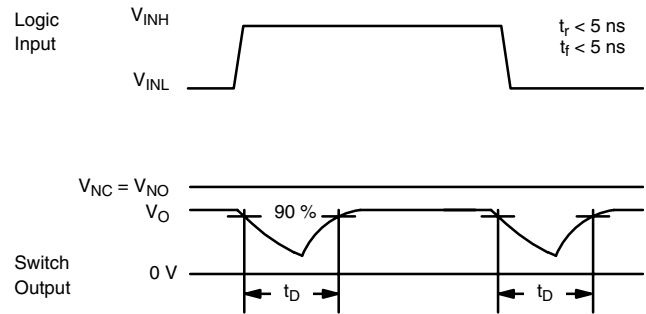
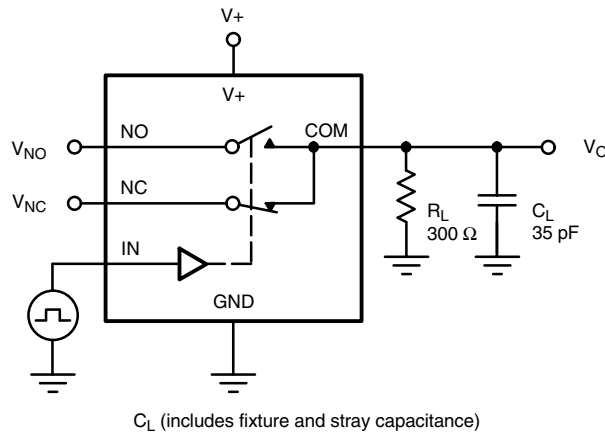
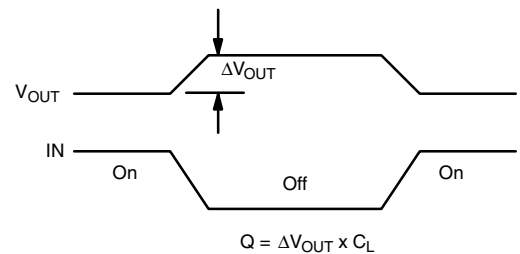
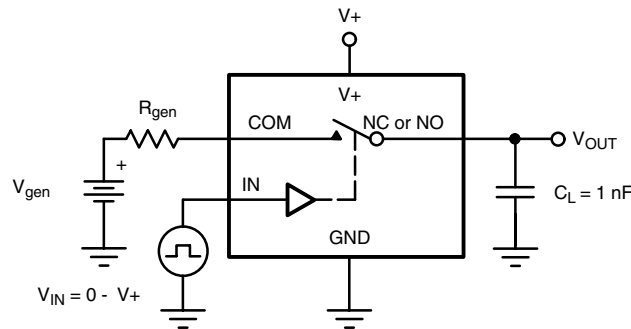
Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage

TEST CIRCUITS


Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

Figure 2. Break-Before-Make Interval


IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

TEST CIRCUITS

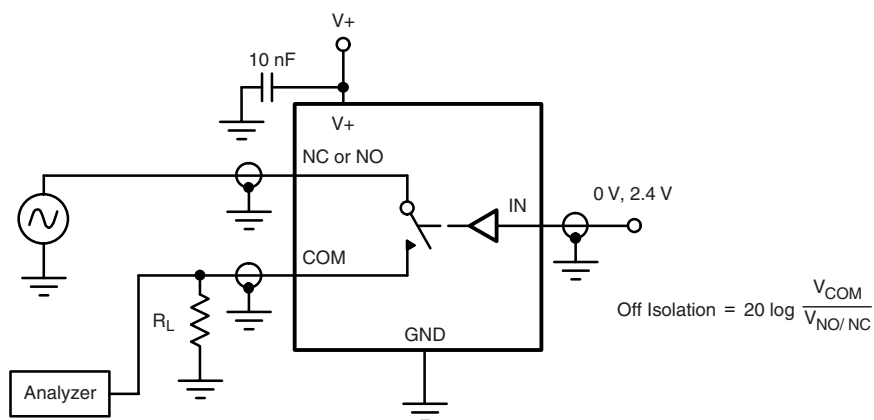


Figure 4. Off-Isolation

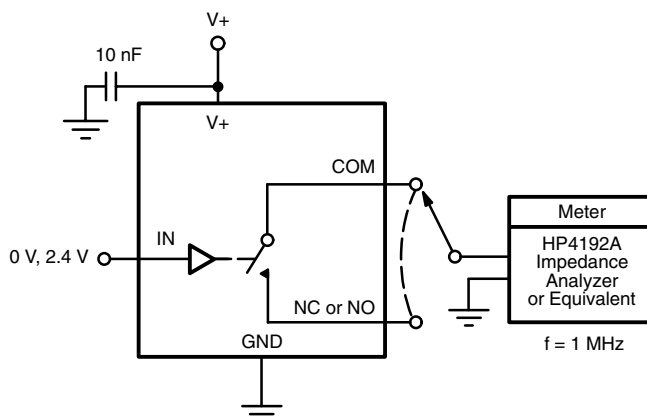
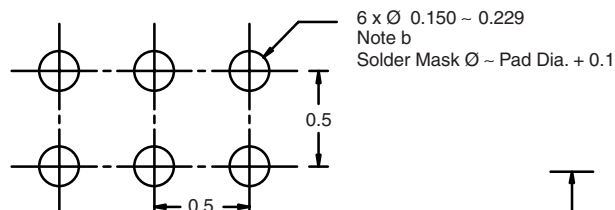


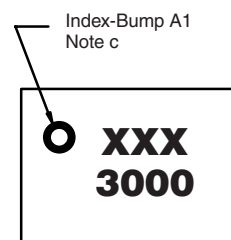
Figure 5. Channel Off/On Capacitance

PACKAGE OUTLINE

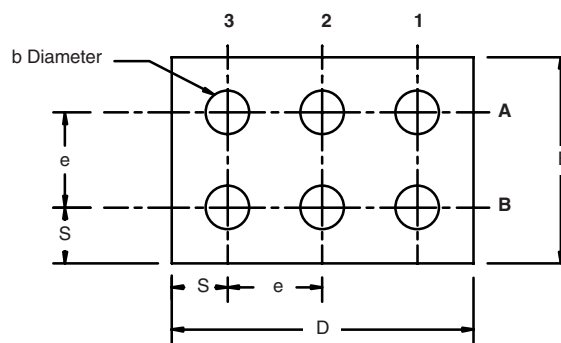
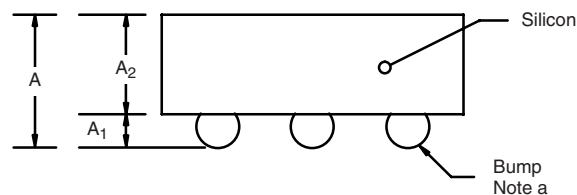
MICRO FOOT: 6-BUMP (3 x 2, 0.5 mm PITCH)



Recommended Land Pattern



Top Side (Die Back)



Notes (Unless Otherwise Specified):

- a. Bump is Eutectic 63/57 Sn/Pb or Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser Mark on silicon die back; no coating. Shown is not actual marking; sample only.

EUTECTIC (Sn/Pb)				
Dim	Millimeters ^a		Inches	
	Min	Max	Min	Max
A	0.615	0.715	0.0242	0.0281
A₁	0.140	0.190	0.0055	0.0075
A₂	0.470	0.495	0.0185	0.0195
b	0.180	0.250	0.0071	0.0098
D	1.555	1.585	0.0612	0.0624
E	1.055	1.085	0.0415	0.0427
e	0.5 BASIC		0.0197 BASIC	
S	0.278	0.293	0.0109	0.0115

Notes:

- a. Use millimeters as the primary measurement.

LEAD (Pb)-FREE (Sn/Ag/Cu)				
Dim	Millimeters ^a		Inches	
	Min	Max	Min	Max
A	0.688	0.753	0.0271	0.0296
A₁	0.218	0.258	0.0086	0.0102
A₂	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.555	1.585	0.0612	0.0624
E	1.055	1.085	0.0415	0.0427
e	0.5 BASIC		0.0197 BASIC	
S	0.278	0.293	0.0109	0.0115

Notes:

- a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?71742>.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9